

Biophysical Foundations

BENG/BGGN 260 Neurodynamics

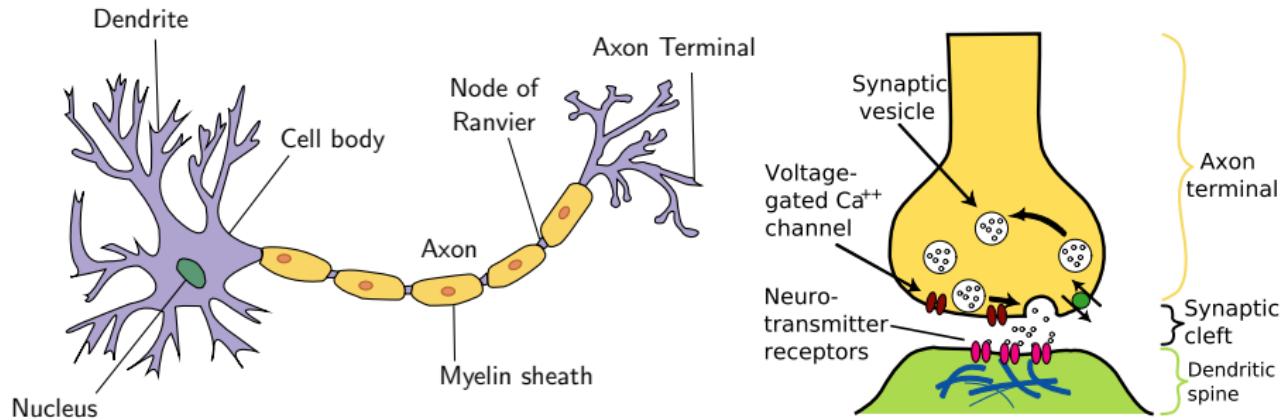
University of California, San Diego

Week 1

Reading Material

- B. Hille, *Ion Channels of Excitable Membranes*, Sinauer, 2001, Ch. 1 and 10, pp. 1-21 and 309-326.
- C. Koch, *Biophysics of Computation*, Oxford Univ. Press, 1999, Ch. 1, pp. 5-13.
- P. Dayan and L. Abbott, *Theoretical Neuroscience*, MIT Press, 2001, Ch. 5, pp. 153-162.
- E.M. Izhikevich, *Dynamical Systems in Neuroscience*, MIT Press, 2007, Ch. 2, pp. 25-28.

Neurodynamics: Overview



Membrane Dynamics

Action Potential Generation

$\sim 1 \text{ ms}$

Temporal Coding Signal Propagation

Axon Dynamics

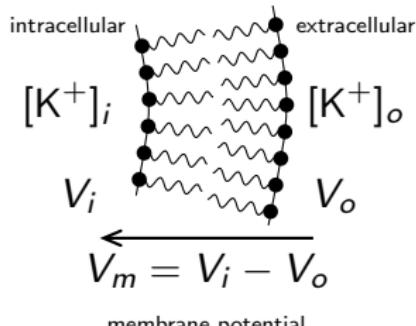
$\sim 10 - 100 \text{ ms}$

Adaptation and Learning

STDP, reinforcement, ...

$\sim 1 \text{ s} - \text{years}$

Nernst Potential



$$\frac{[K^+]_o}{[K^+]_i} = \frac{n_o}{n_i} = e^{-\frac{\varepsilon_o - \varepsilon_i}{kT}} \quad (= e^{-\frac{U_o - U_i}{RT}})$$

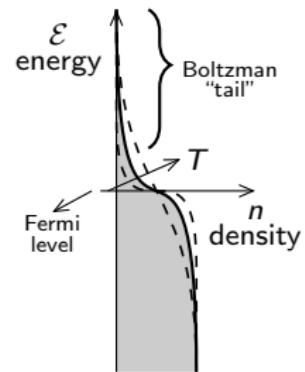
density ratio energies per molecule energies per mol
 Boltzman constant absolute temperature gas constant

$$= e^{-\frac{V_o - V_i}{kT/q}}$$

charge per molecule
 $= 1.6 \cdot 10^{-19} \text{ C}$ per valence index

$$\Rightarrow E_{rest} = V_m|_{equilibrium} = \frac{kT}{q} \ln \frac{[K^+]_o}{[K^+]_i}$$

$$= \underbrace{\frac{kT}{q} \ln 10}_{62 \text{mV } @ \text{ room T}} \log_{10} \frac{[K^+]_o}{[K^+]_i}$$



Nernst Potential

TABLE 1.3 Free Ion Concentrations and Equilibrium Potentials for Mammalian Skeletal Muscle

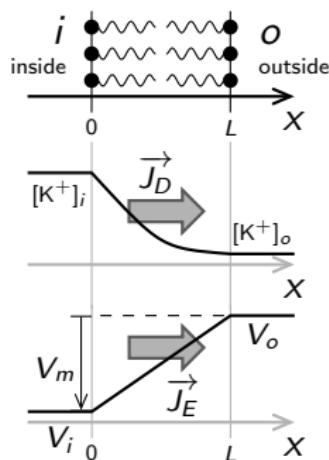
| Ion | Extracellular concentration (mM) | Intracellular concentration (mM) | $\frac{[ion_o]}{[ion_i]}$ | Equilibrium potential ^a (mV) |
|------------------|-------------------------------------|-------------------------------------|---------------------------|--|
| Na ⁺ | 145 | 12 | 12 | +67 |
| K ⁺ | 4 | 155 | 0.026 | -98 |
| Ca ²⁺ | 1.5 | 100 nM | 15,000 | +129 |
| Cl ⁻ | 123 | 4.2 ^b | 29 ^b | -90 ^b |

^a Calculated from Equation 1.11 at 37°C ($E_{rest} = \frac{kT}{q} \ln \frac{[ion_o]}{[ion_i]}$).

^b Calculated assuming a -90-mV resting potential for the muscle membrane and that Cl⁻ ions are at equilibrium at rest.

Hille 2001, p. 17

Nernst-Planck



Diffusion: $\vec{J}_D = qD \cdot (-\vec{\nabla}[K^+])$

Drift: $\vec{J}_E = q[K^+] \mu \cdot \vec{E} = q\mu[K^+] (-\vec{\nabla} V)$

$$\Rightarrow \vec{J}_{K^+} = \vec{J}_D + \vec{J}_E = 0 \quad \text{equilibrium}$$

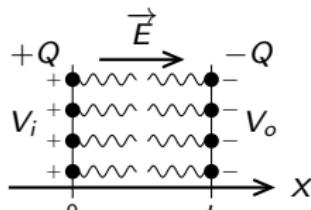
$$\Rightarrow -qD \frac{d[\text{K}^+]}{dx} - q\mu[\text{K}^+] \frac{dV}{dx} = 0 \Rightarrow \frac{D}{\mu} \frac{d[\text{K}^+]}{[\text{K}^+]} \underset{d(\ln [\text{K}^+])}{=} -dV$$

$$\Rightarrow \frac{D}{\mu} \ln \frac{[\text{K}^+]_o}{[\text{K}^+]_i} = - (V_o - V_i) = V_m = E_{rest} \text{ with } \frac{D}{\mu} = \frac{kT}{q}$$

indeed, $D = \frac{kT}{q} \cdot \mu$

Dissipation-fluctuation (Einstein)

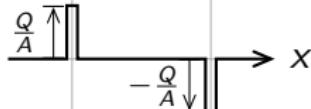
Membrane Capacitance



capacitance = differential charge accumulation with voltage across insulator (membrane)

Charge Density

$$\rho$$



Electric Field

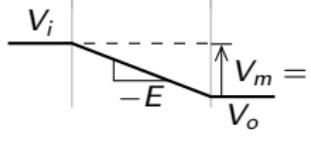
$$\vec{E}$$



$$\vec{\nabla} \vec{E} = \frac{\rho}{\epsilon}, \text{ or } \frac{d\vec{E}}{dx} = \frac{\rho}{\epsilon}$$

Potential V

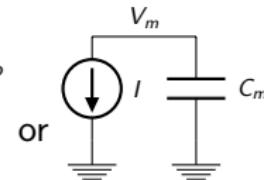
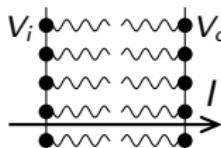
$$V$$



$$\vec{\nabla} V = -\vec{E}, \text{ or } \frac{dV}{dx} = -E$$

$$Q = C_m \cdot V_m \text{ with } C_m = \epsilon \cdot \frac{A}{L} \quad \frac{\epsilon}{L} \approx 0.01 \text{ F/m}^2$$

Dynamics:



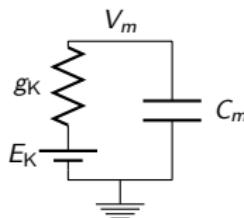
$$: C_m \frac{dV_m}{dt} = -I(V_m, \dots)$$

Membrane Dynamics

- K^+ : current density $\vec{J}_K = -q\mu[K] \left(\frac{kT}{q} \vec{\nabla} \ln[K] + \vec{\nabla} V \right)$

↓ approximate arguments ... more rigorous later

$$\text{current } I_K \approx -q\mu[\bar{K}] \frac{A}{L} \left(\frac{kT}{q} \ln \frac{[K]_o}{[K]_i} + V_o - V_i \right) = g_K (V_m - E_K)$$

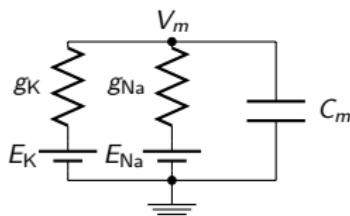


average concentration membrane thickness effective cross-section

$$\begin{cases} g_K = q\mu[\bar{K}] \frac{A}{L} \\ E_K = \frac{kT}{q} \ln \frac{[K]_o}{[K]_i} \end{cases}$$

Ohmic approximation

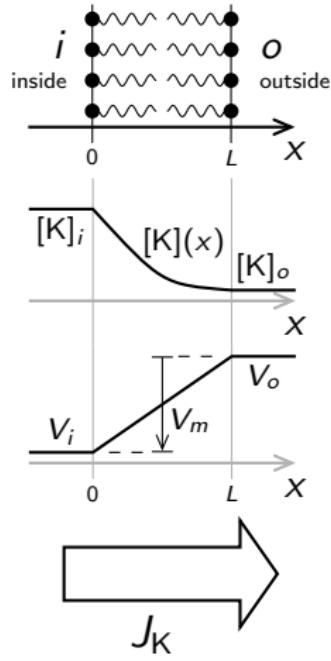
- K^+, Na^+ :



$$\text{Equilibrium: } E_{rest} = V_m = \frac{g_K E_K + g_{Na} E_{Na}}{g_K + g_{Na}}$$

Not quite...

Goldman-Hodgkin-Katz



$$\vec{J}_K = -q\mu \left(\frac{kT}{q} \vec{\nabla} [K] + [K] \vec{\nabla} V \right)$$

CURRENT
DENSITY, $\mu A/cm^2$ DIFFUSION DRIFT

1-D, along x perpendicular to membrane:

$$J_K = -q\mu \left(\frac{kT}{q} \frac{d[K]}{dx} + [K] \frac{dV}{dx} \right)$$

- $J_K = \text{constant}$ (flow conservation)
- $\frac{dV}{dx} = \text{constant}$ (assumption!)
 $= -\frac{V_m}{L}$

$$\Rightarrow \frac{kT}{q} \frac{d[K]}{dx} = -\frac{J_K}{q\mu} + \frac{V_m}{L} \cdot [K]$$

Goldman-Hodgkin-Katz Continued

$$\frac{kT}{q} \frac{d[K]}{dx} = -\frac{J_K}{q\mu} + \frac{V_m}{L} \cdot [K] \Rightarrow \frac{d[K]}{-\frac{J_K}{q\mu} + \frac{V_m}{L} \cdot [K]} = \frac{dx}{\frac{kT}{q}} \Rightarrow$$

$$\frac{L}{V_m} d \left[\ln \left(-\frac{J_K}{q\mu} + \frac{V_m}{L} \cdot [K] \right) \right] = \frac{dx}{\frac{kT}{q}} \Rightarrow \frac{V_m}{\frac{kT}{q}} = \ln \frac{-J_K + \frac{q\mu V_m}{L} [K]_o}{-J_K + \frac{q\mu V_m}{L} [K]_i} \Rightarrow$$

$$J_K \left(1 - e^{-V_m / \frac{kT}{q}} \right) = \frac{q\mu V_m}{L} \left([K]_i - e^{-V_m / \frac{kT}{q}} [K]_o \right) \Rightarrow$$

$$J_K = \frac{q\mu V_m}{L} \cdot \frac{[K]_i - e^{-V_m / \frac{kT}{q}} [K]_o}{1 - e^{-V_m / \frac{kT}{q}}}$$

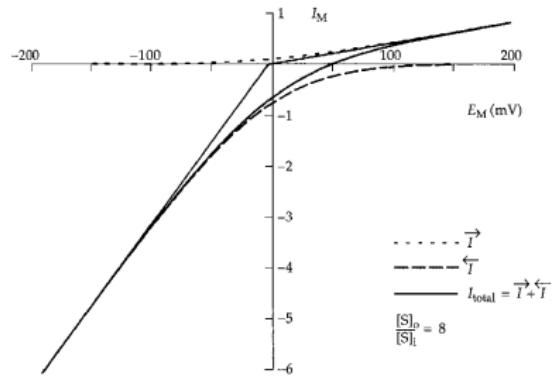
“GHK current equation”

Ohm's limit: $[K]_i = [K]_o = [K]$

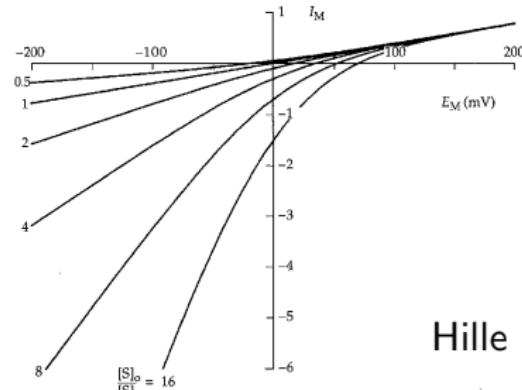
$$\Rightarrow J_K = \frac{q\mu V_m}{L} \cdot [K]$$

Goldman-Hodgkin-Katz Current Law

(A) UNIDIRECTIONAL FLUXES



(B) CONCENTRATION DEPENDENCE



Hille 2001, Fig. 14.2, p. 447

Goldman-Hodgkin-Katz Limits

$$J_K = \frac{q\mu_K V_m}{L} \cdot \frac{[K]_i - e^{-V_m/V_t}[K]_o}{1 - e^{-V_m/V_t}} \quad V_t = \frac{kT}{q} \approx 25.9mV$$

- ① $J_K = 0$ for $[K]_i = e^{-V_m/V_t}[K]_o$, or $V_m = V_t \ln \frac{[K]_o}{[K]_i} = E_K$ (OK!)

② $J_K \begin{cases} \xrightarrow{V_m \gg V_t} \frac{q\mu_K}{L} [K]_i V_m = P_K [K]_i V_m & P_K = \frac{q\mu_K}{L} \\ \xrightarrow{V_m \ll -V_t} \frac{q\mu_K}{L} [K]_o V_m = P_K [K]_o V_m & \text{"permeability"} \end{cases}$

\Rightarrow Current asymptotes to a linear conductance limited by the **sourcing** concentration at active terminal.

- ③ $J_K \approx g_K(V_m - E_K)$ for $J_K \approx 0$ ($V_m \approx E_K$) ?

GHK Ohmic Approximation

$$V_m \approx E_K = \frac{kT}{q} \ln \frac{[K]_o}{[K]_i} \Rightarrow e^{-\frac{V_m}{kT}} = e^{-\frac{E_K}{kT}} e^{-\frac{V_m - E_K}{kT}} \approx \frac{[K]_i}{[K]_o} \left(1 - \frac{V_m - E_K}{kT} \right)$$

$$\Rightarrow J_K \approx \frac{q\mu E_K}{L} \cdot \frac{\frac{[K]_i}{[K]_o} \left(1 - \frac{V_m - E_K}{kT} \right) \cdot [K]_o}{1 - \frac{[K]_i}{[K]_o} \left(1 - \frac{V_m - E_K}{kT} \right)}$$

or: $J_K \approx g_K (V_m - E_K)$

with $\underbrace{g_K}_{\text{channel conductance}} = \underbrace{\frac{q\mu}{L}}_{\text{permeability}} \cdot \underbrace{\ln \frac{[K]_o}{[K]_i}}_{\text{average concentration}} \cdot \underbrace{\frac{[K]_i [K]_o}{[K]_o - [K]_i}}$

Goldman-Hodgkin-Katz Equilibrium

$$J_K = \frac{q\mu_K V_m}{L} \quad \frac{[K]_i - e^{-\frac{V_m}{kT/q}} [K]_o}{1 - e^{-\frac{V_m}{kT/q}}}$$

$$J_{Na} = \frac{q\mu_{Na} V_m}{L} \quad \frac{[Na]_i - e^{-\frac{V_m}{kT/q}} [Na]_o}{1 - e^{-\frac{V_m}{kT/q}}}$$

Equilibrium : $J_K + J_{Na} \equiv 0$, neglecting common terms :

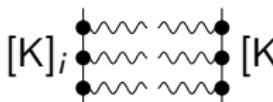
$$\mu_K \left([K]_i - e^{-\frac{V_m}{kT/q}} [K]_o \right) + \mu_{Na} \left([Na]_i - e^{-\frac{V_m}{kT/q}} [Na]_o \right) \equiv 0$$

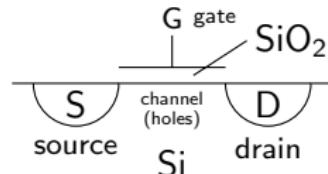
$$E_{rest} = V_m = \frac{kT}{q} \ln \frac{\mu_K [K]_o + \mu_{Na} [Na]_o}{\mu_K [K]_i + \mu_{Na} [Na]_i}$$

usually expressed in terms of permeabilities:

$$P_K = \frac{q\mu_K}{L} \text{ and } P_{Na} = \frac{q\mu_{Na}}{L}$$

GHK Neuromorphism (for the silicon enthusiast)

LIPID BILAYER :  $[K]_i$ $[K]_o$ $J_K \cong \begin{cases} P_K[K]_i & \text{for } V_m \gg V_t \\ P_K[K]_o & \text{for } V_m \ll -V_t \end{cases}$

SILICON MOSFET :  $J_p \cong \begin{cases} J_0 e^{\kappa \frac{V_g}{V_t}} \cdot e^{\frac{V_s}{V_t}} & \text{for } V_{ds} \gg V_t \\ J_0 e^{\kappa \frac{V_g}{V_t}} \cdot e^{\frac{V_d}{V_t}} & \text{for } V_{ds} \ll -V_t \end{cases}$

neuromorphisms :
(imperfect)

| | |
|--|---|
| $P_K \rightarrow J_0 e^{\kappa \frac{V_g}{V_t}}$ | controlled by V_g , gate voltage |
| $[K]_i \rightarrow e^{-\frac{V_s}{V_t}}$ | controlled by V_s , source voltage |
| $[K]_o \rightarrow e^{-\frac{V_d}{V_t}}$ | controlled by V_d , drain voltage |
| $V_m \rightarrow V_{ds} = V_d - V_s$, i.e. : | |
| $V_i \rightarrow -V_s$ | |
| $V_o \rightarrow -V_d$ | |

* C.A. Mead, *Analog VLSI and Neural Systems*, Addison-Wesley, 1989